



FUKUCOM COMPANY LTD.

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FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

LL103A...LL103C

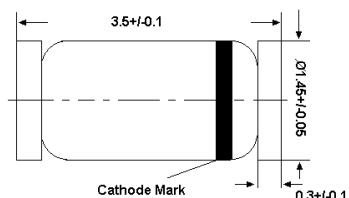
Silicon Schottky Barrier Diodes

for general purpose applications

The LL103A, B, C is a metal on Silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications. Other uses are for click suppression, efficient full wave bridges in telephone subsets, and as blocking diodes in rechargeable low voltage battery systems.

This diode is also available in DO-35 case with type designation SD103A, B, C.

LL-34



Glass case MiniMELF

Dimensions in mm

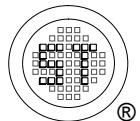
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage LL103A LL103B LL103C	V_{RRM}	40	V
		30	
		20	
Single Cycle Surge 60 Hz sinewave	I_{FSM}	15	A
Power Dissipation (Infinite Heatsink) $T_c = 3/8$ from body Derates at 4 mW/ $^\circ\text{C}$ to 0 at 125°C	P_{tot}	400 ¹⁾	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^\circ\text{C}$

¹⁾ Valid provided that electrodes are kept at ambient temperature.

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Typ.	Max.	Unit
Forward Voltage				
Forward Voltage at $I_F = 20$ mA at $I_F = 200$ mA	V_F	- -	0.37 0.6	V
Reverse Current at $V_R = 30$ V at $V_R = 20$ V at $V_R = 10$ V	I_R	-	5	μA
		-	5	
		-	5	
Total Capacitance at $V_R = 0$ V, $f = 1$ MHz	C_{tot}	50	-	pF
Reverse Recovery Time at $I_F = I_R = 5$ mA to 200 mA, recover to 0.1 I_R	t_{rr}	10	-	ns



Dated : 02/09/2010 Rev:01



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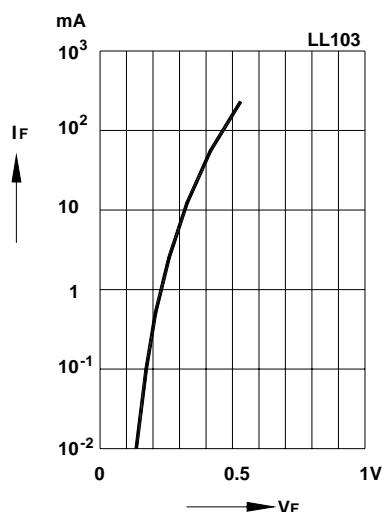
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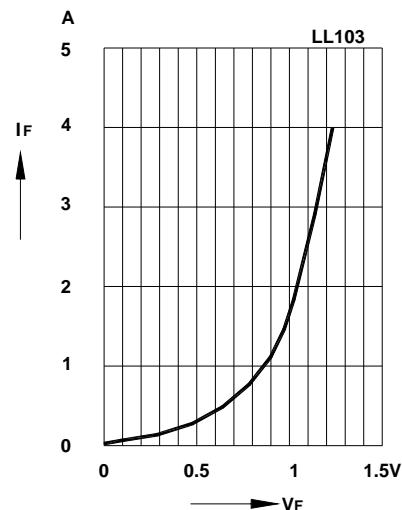
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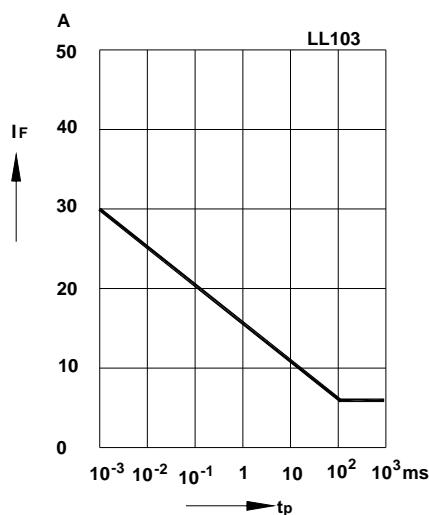
Typical variation of fwd. current
vs.fwd.voltage for primary conduction
through the Schottky barrier



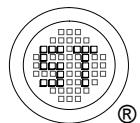
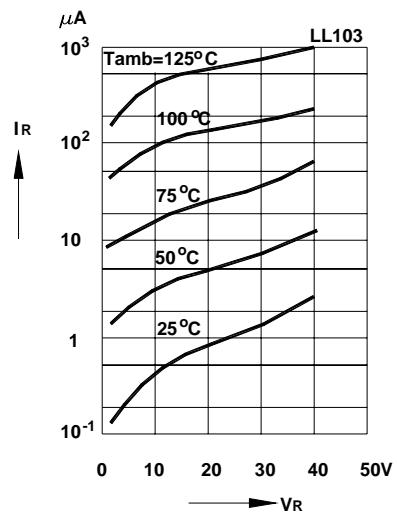
Typical high current forward
conduction curve
 $t_p=300\mu s$, duty cycle=2%



Typical non repetitive forward surge
current versus pulse width
Rectangular pulse



Typical variation of reverse current
at various temperatures





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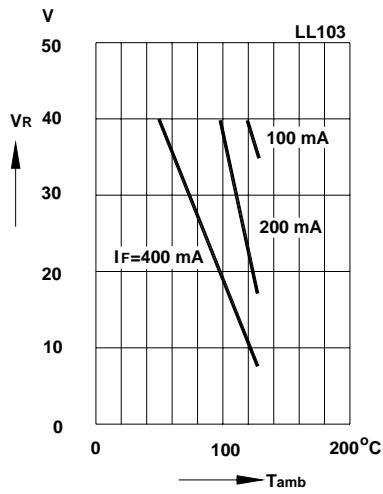
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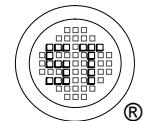
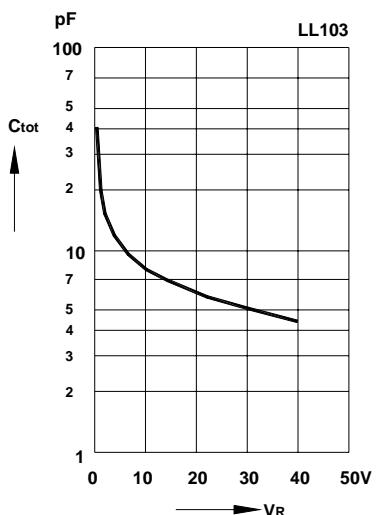
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**Blocking voltage deration
versus temperature at various
average forward currents**



**Typical capacitance
versus reverse voltage**



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